TOLL-8L N
N-Channel MOSFET in a TOLL-8L Plastic Package.

V_{DS}(V)=100V I_D=292A
$R_{DS(ON)}$@10V≤1.9mΩ(Typ.1.6mR)
Â HF Product.

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Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Drain Current - Continuous	I_D	292	A
Drain Current - Continuous	I_D(T_c=100℃)	292	A
Drain Current – Pulsed	I_{DM}	1168	A
Gate-Source Voltage	V_{GS}	¤ 20	V
Power Dissipation	P_{tot}	312.5	W
Continuous-Source Current	I_S	292	A
Single Pulse Avalanche Energy(V_{DD}=50V,L=1mH)		EmJ880.3(A)]TJET 7.02 678.44 481.32 .47998 ref555.62	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V V_{DS}=50V R_L=1 ß R_G=3.9 ß I_{DS}=50A		59		ns
Turn-On Rise Time	t_r			66		
Turn-Off Delay Time	$t_{d(off)}$			185		
Turn-Off Fall Time	t_f			95		
Reverse Recovery Time	t_{rr}	I_{DS} = 50 A, V_{GS} = 0 V dI_{SD}/dt = 100 A/ ë s		66		nS
Reverse Recovery Charge	Q_{rr}					

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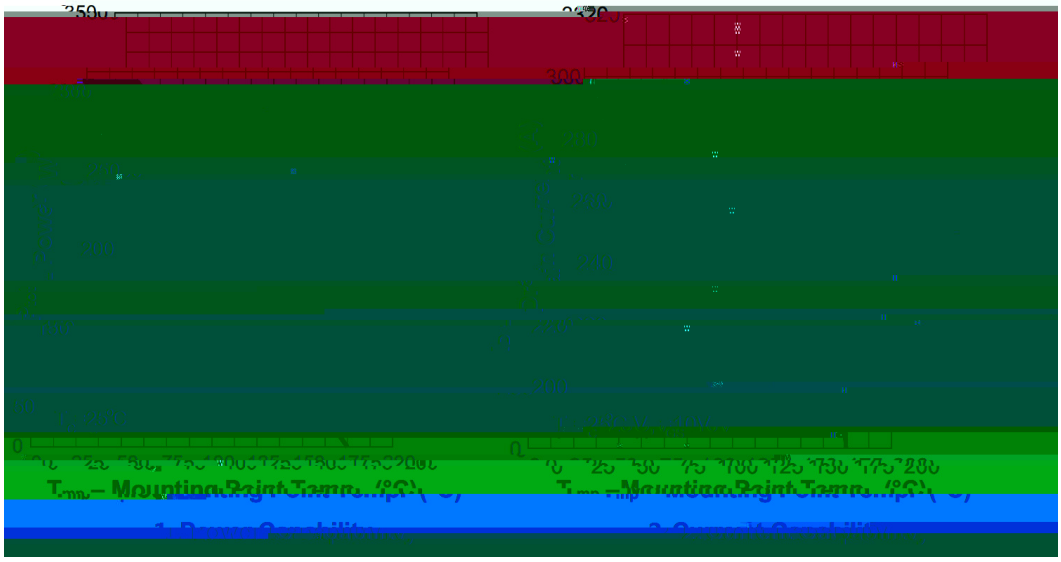

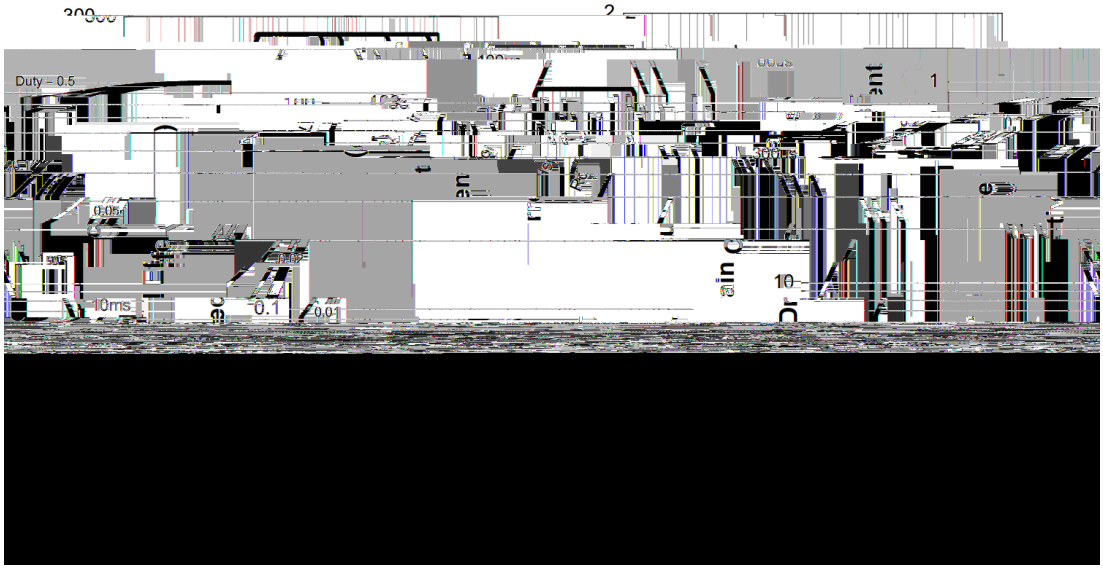



5. Output Characteristics **6. On Resistance**

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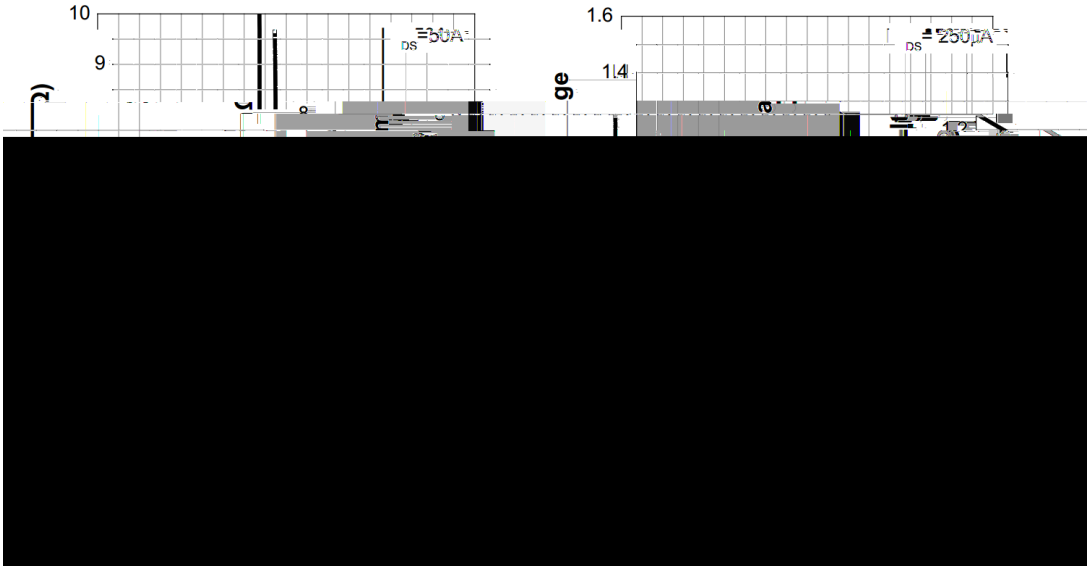
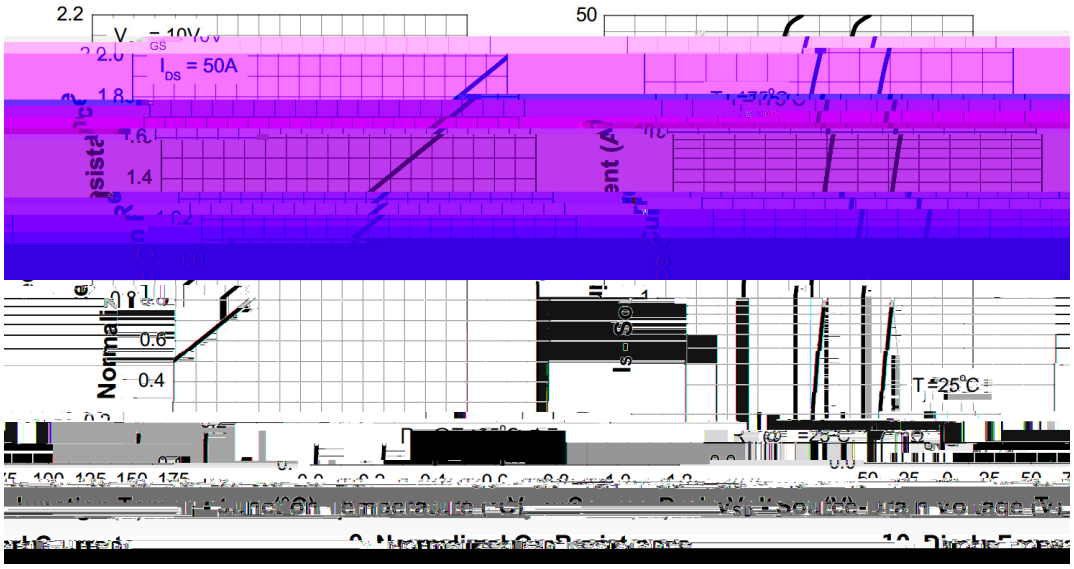
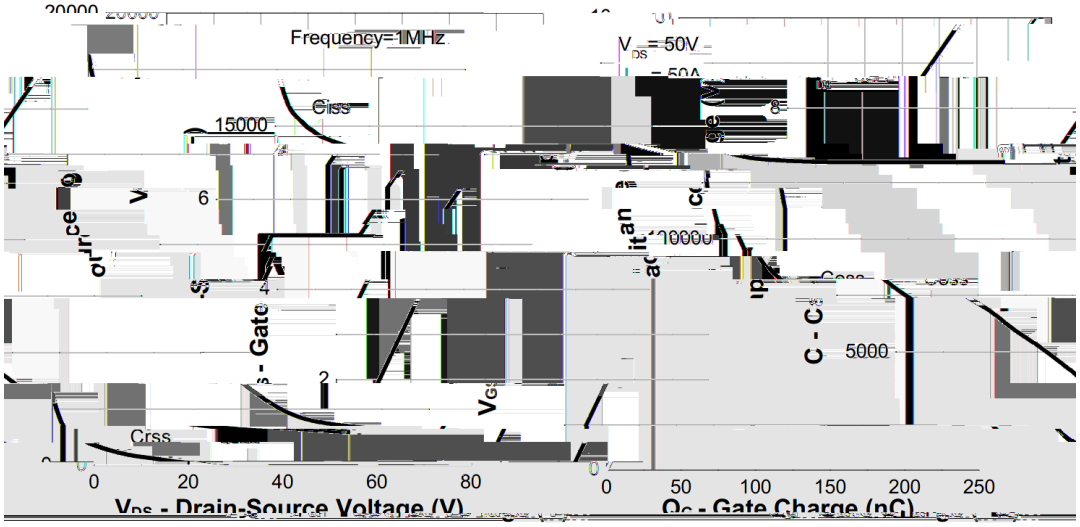
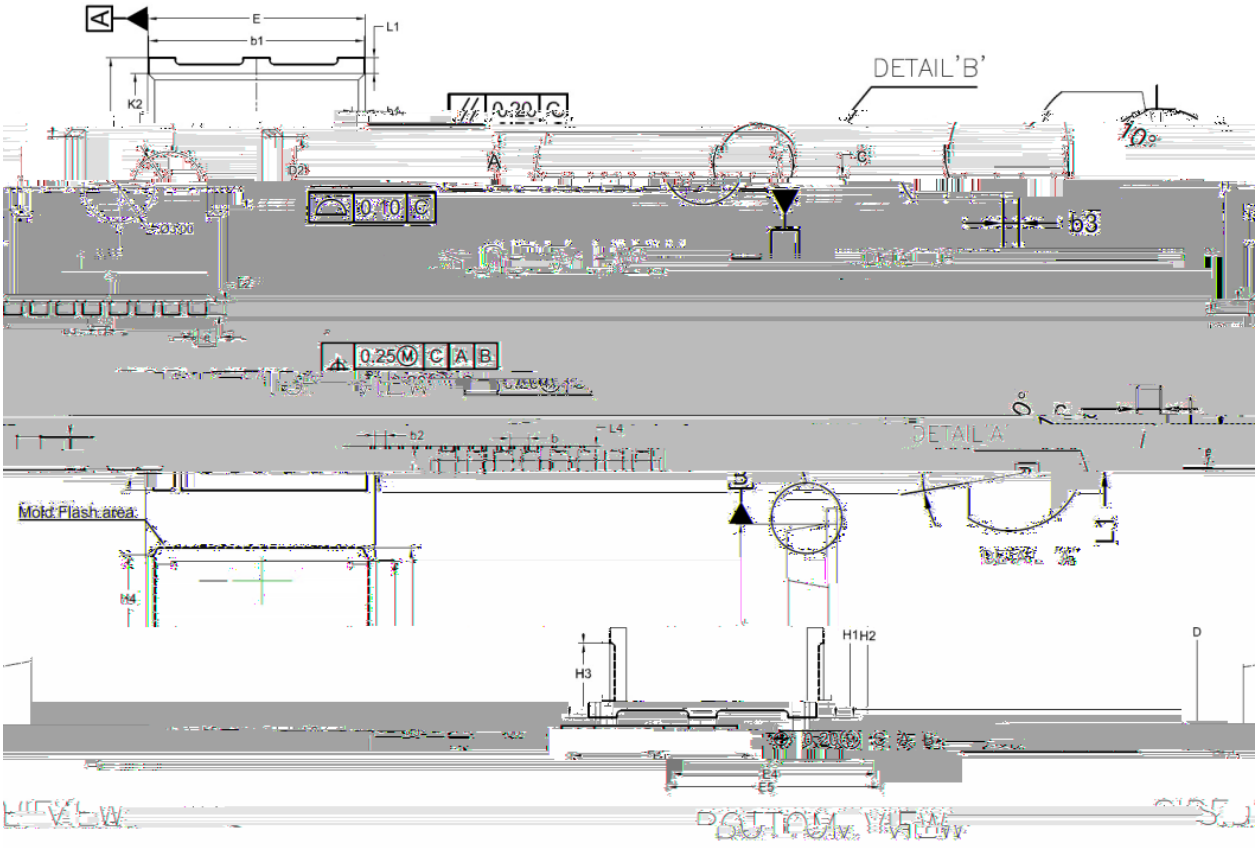






11. Capacitance **12. Gate Charge**

ᵘ ĖÒĻ ƒ / Package Dimensions



V|per0	Gl p hqvlrqv Lq P lool p hwhuv			V|per0	Gl p hqvlrqv Lq P lool p hwhuv		
	PLQ1	QRP1	PD[1		PLQ1	QRP1	PD[1
A	2.200	2.300	2.400	b1	9.700	9.800	9.900
c	0.492	0.500	0.508	b1	0.420	0.460	0.500
D	10.280	10.380	10.480	b3		0.350	
E	9.800	9.900	10.000	b4		0.600	
e		1.20 BSC		b5		3.100	
H	11.580	11.680	11.780	b6		1.200	
H1	6.650	6.750	6.850	L	1.700	1.900	2.100
H2		7.300		L1		0.700	
H3		3.200		L2		0.600 H я	